

Pin Description and Pin Characteristic Tables

Table 1. Pin Descriptions

Number	Name	Type		Description
1, 9, 13	GND	Power		Power supply ground.
2	CLK_EN	Input	Pullup	Synchronizing clock enable. When HIGH, clock outputs follows clock input. When LOW, Q outputs are forced low, $\overline{Q}$ outputs are forced high. LVCMOS / LVTTTL interface levels.
3	CLK_SEL	Input	Pulldown	Clock select input. When HIGH, selects CLK2 input. When LOW, selects CLK1 input. LVCMOS / LVTTTL interface levels.
4	CLK1	Input	Pulldown	Single-ended clock input. LVCMOS/LVTTTL interface levels.
5, 7	nc	Unused		No connect.
6	CLK2	Input	Pulldown	Single-ended clock input. LVCMOS/LVTTTL interface levels.
8	OE	Input	Pullup	Output enable. Controls enabling and disabling of outputs Q0/ $\overline{Q0}$ through Q3/ $\overline{Q3}$. LVCMOS/LVTTTL interface levels.
10, 18	V _{DD}	Power		Positive supply pins.
11, 12	$\overline{Q3}$, Q3	Output		Differential output pair. LVDS interface levels.
14, 15	$\overline{Q2}$, Q2	Output		Differential output pair. LVDS interface levels.
16, 17	$\overline{Q1}$, Q1	Output		Differential output pair. LVDS interface levels.
19, 20	$\overline{Q0}$, Q0	Output		Differential output pair. LVDS interface levels.

NOTE: *Pullup* and *Pulldown* refer to internal input resistors. See Table 2, *Pin Characteristics*, for typical values.

Table 2. Pin Characteristics

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
C _{IN}	Input Capacitance			4		pF
R _{PULLUP}	Input Pullup Resistor			51		k Ω
R _{PULLDOWN}	Input Pulldown Resistor			51		k Ω

Function Tables

Table 3A. Control Input Function Table

Inputs				Outputs	
OE	CLK_EN	CLK_SEL	Selected Source	Q0:Q3	$\overline{Q0:Q3}$
0	X	X		Hi-Z	Hi-Z
1	0	0	CLK1	Low	High
1	0	1	CLK2	Low	High
1	1	0	CLK1	Active	Active
1	1	1	CLK2	Active	Active

After CLK_EN switches, the clock outputs are disabled or enabled following a rising and falling input clock edge as shown in Figure 1. In the active mode, the state of the outputs are a function of the CLK1 and CLK2 inputs as described in Table 3B.

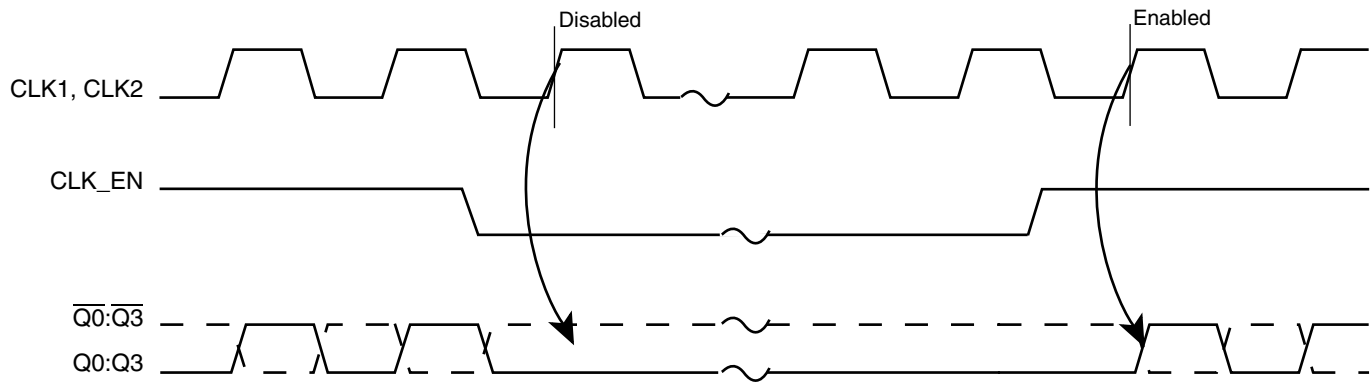


Figure 1. CLK_EN Timing Diagram

Table 3B. Clock Input Function Table

Inputs	Outputs	
CLK1 or CLK2	Q0:Q3	$\overline{Q0:Q3}$
0	LOW	HIGH
1	HIGH	LOW

Absolute Maximum Ratings

NOTE: Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These ratings are stress specifications only. Functional operation of product at these conditions or any conditions beyond those listed in the *DC Characteristics* or *AC Characteristics* is not implied. Exposure to absolute maximum rating conditions for extended periods may affect product reliability.

Item	Rating
Supply Voltage, V_{DD}	4.6V
Inputs, V_I	-0.5V to $V_{DD} + 0.5V$
Outputs, I_O Continuous Current Surge Current	10mA 15mA
Package Thermal Impedance, θ_{JA}	73.2°C/W (0 lfpm)
Storage Temperature, T_{STG}	-65°C to 150°C

DC Electrical Characteristics

Table 4A. Power Supply DC Characteristics, $V_{DD} = 3.3V \pm 5\%$, $T_A = -40^\circ C$ to $85^\circ C$

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V_{DD}	Positive Supply Voltage		3.135	3.3	3.465	V
I_{DD}	Power Supply Current				52	mA

Table 4B. LVCMOS/LVTTL DC Characteristics, $V_{DD} = 3.3V \pm 5\%$, $T_A = -40^\circ C$ to $85^\circ C$

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V_{IH}	Input High Voltage		2		$V_{DD} + 0.3$	V
V_{IL}	Input Low Voltage	CLK1, CLK2	-0.3		1.3	V
		OE, CLK_EN, CLK_SEL	-0.3		0.8	V
I_{IH}	Input High Current	CLK1, CLK2, CLK_SEL	$V_{DD} = V_{IN} = 3.465V$		150	μA
		OE, CLK_EN	$V_{DD} = V_{IN} = 3.465V$		5	μA
I_{IL}	Input Low Current	CLK1, CLK2, CLK_SEL	$V_{DD} = 3.465V, V_{IN} = 0V$	-5		μA
		OE, CLK_EN	$V_{DD} = 3.465V, V_{IN} = 0V$	-150		μA

Table 4C. LVDS DC Characteristics, $V_{DD} = 3.3V \pm 5\%$, $T_A = -40^{\circ}C$ to $85^{\circ}C$

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V_{OD}	Differential Output Voltage		200	280	360	mV
ΔV_{OD}	V_{OD} Magnitude Change				40	mV
V_{OS}	Offset Voltage		1.125	1.25	1.375	V
ΔV_{OS}	V_{OS} Magnitude Change			5	25	mV
I_{OZ}	High Impedance Leakage		-10	± 1	+10	μA
I_{OFF}	Power Off Leakage		-20	± 1	+20	μA
I_{OSD}	Differential Output Short Circuit Current			-3.5	-5	mA
I_{OS}	Output Short Circuit Current			-3.5	-5	mA
V_{OH}	Output Voltage High			1.34	1.6	V
V_{OL}	Output Voltage Low		0.9	1.06		V

AC Electrical Characteristics

Table 5. AC Characteristics, $V_{DD} = 3.3V \pm 5\%$, $T_A = -40^{\circ}C$ to $85^{\circ}C$

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
f_{MAX}	Output Frequency				650	MHz
t_{PD}	Propagation Delay; NOTE 1	$f \leq 650MHz$	1.4		3.6	ns
η_{jit}	Buffer Additive Phase Jitter, RMS; refer to Additive Phase Jitter Section	156.25MHz, Integration Range: 12kHz – 20MHz		0.13		ps
$t_{sk(o)}$	Output Skew; NOTE 2, 4				40	ps
$t_{sk(pp)}$	Part-to-Part Skew; NOTE 3, 4				500	ps
t_R / t_F	Output Rise/Fall Time	20% to 80% @ 50MHz	200	400	700	ps
odc	Output Duty Cycle	$f \leq 266MHz$	45		55	%
		$f > 266MHz$	40		60	%

All parameters measured at $f \leq 650MHz$ unless noted otherwise.

NOTE 1: Measured from $V_{DD}/2$ of the input to the differential output crossing point.

NOTE 2: Defined as skew between outputs at the same supply voltage and with equal load conditions.

Measured at $V_{DD}/2$ of the input to the differential output crossing point.

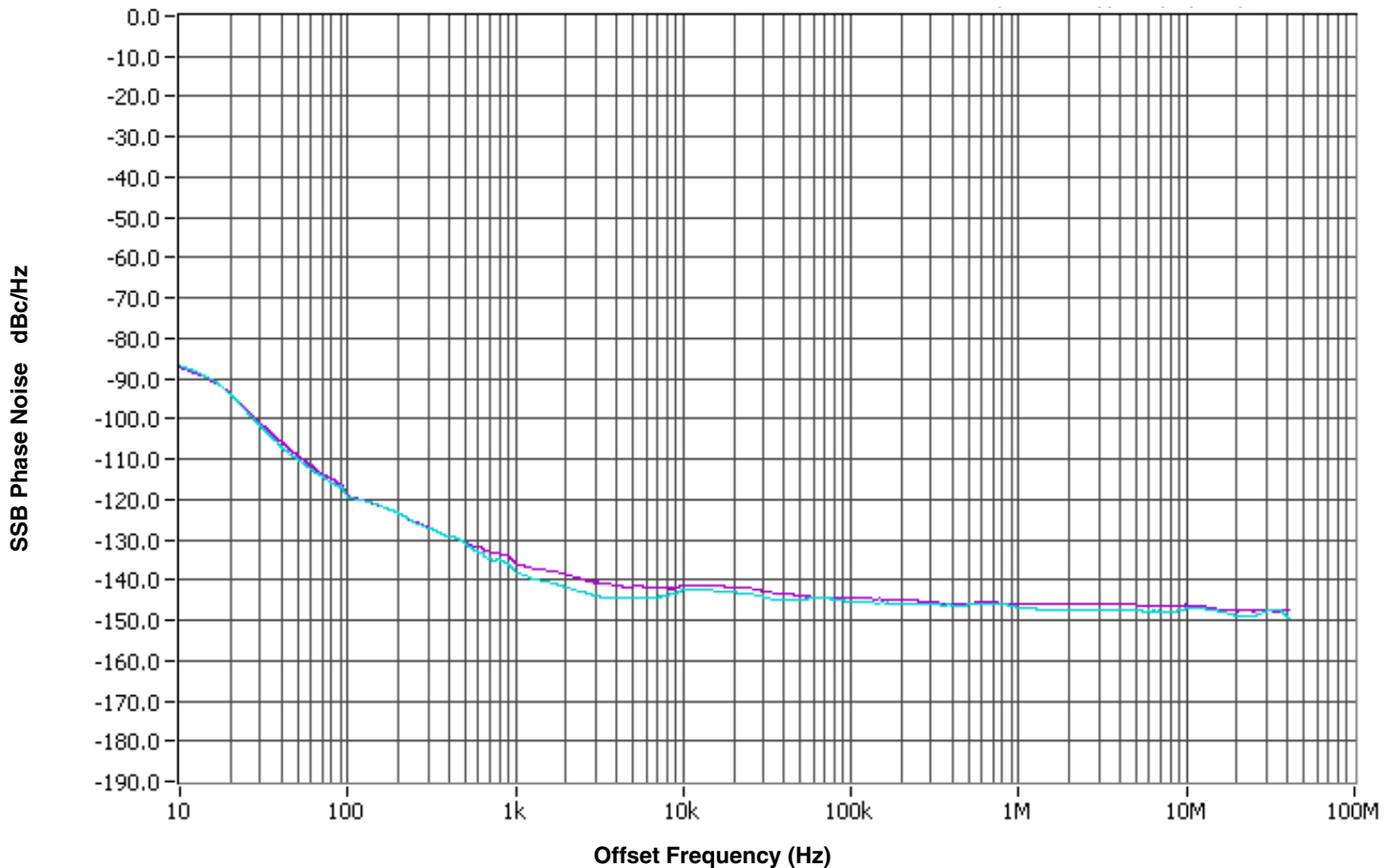
NOTE 3: Defined as skew between outputs on different devices operating at the same supply voltages and with equal load conditions. Using the same type of inputs on each device, the outputs are measured at the differential cross points.

NOTE 4: This parameter is defined in accordance with JEDEC Standard 65.

Additive Phase Jitter

The spectral purity in a band at a specific offset from the fundamental compared to the power of the fundamental is called the ***dBc Phase Noise***. This value is normally expressed using a Phase noise plot and is most often the specified plot in many applications. Phase noise is defined as the ratio of the noise power present in a 1Hz band at a specified offset from the fundamental frequency to the power value of the fundamental. This ratio is expressed in decibels (dBm) or a ratio

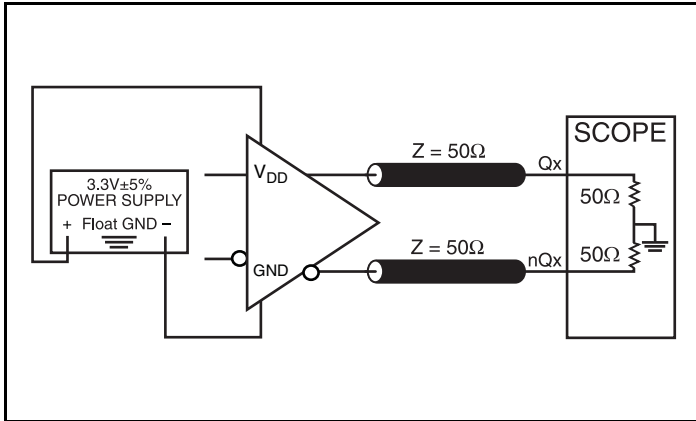
of the power in the 1Hz band to the power in the fundamental. When the required offset is specified, the phase noise is called a ***dBc*** value, which simply means dBm at a specified offset from the fundamental. By investigating jitter in the frequency domain, we get a better understanding of its effects on the desired application over the entire time record of the signal. It is mathematically possible to calculate an expected bit error rate given a phase noise plot.



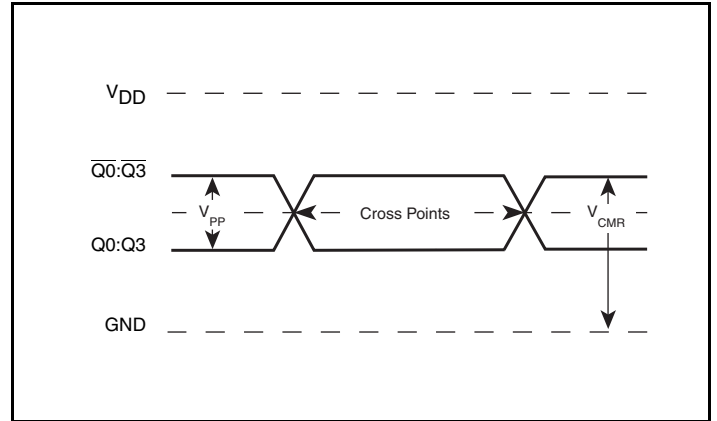
As with most timing specifications, phase noise measurements have issues. The primary issue relates to the limitations of the equipment. Often the noise floor of the equipment is higher than the noise floor

of the device. This is illustrated above. The device meets the noise floor of what is shown, but can actually be lower. The phase noise is dependent on the input source and measurement equipment.

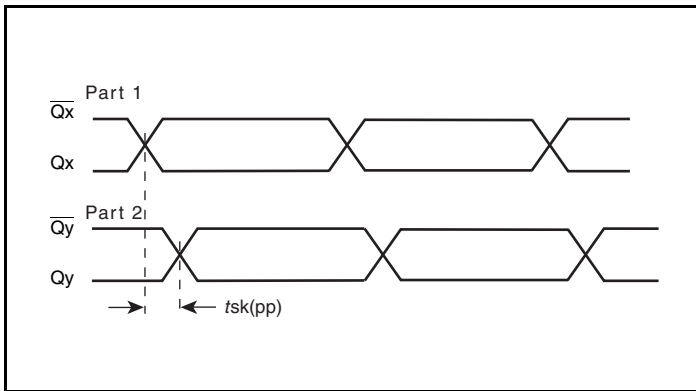
Parameter Measurement Information



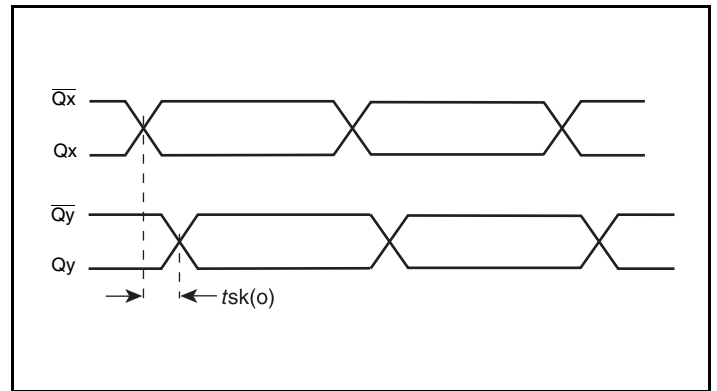
3.3V LVDS Output Load AC Test Circuit



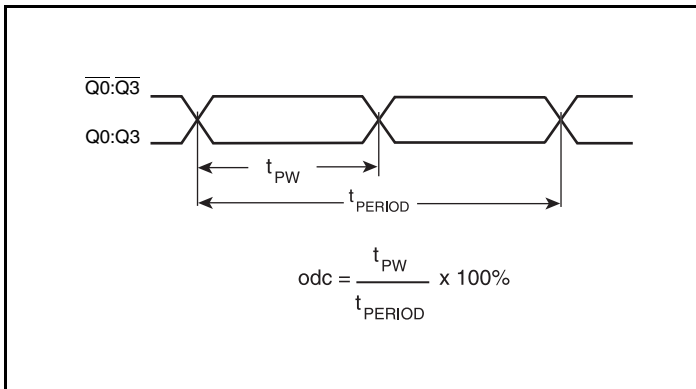
Differential Output Level



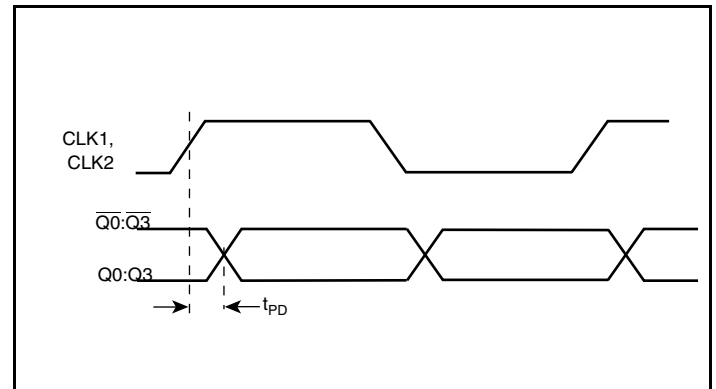
Part-to-Part Skew



Output Skew

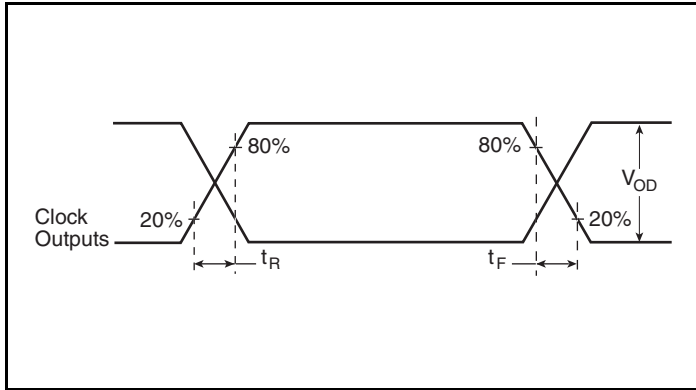


Output Duty Cycle/Pulse Width/Period

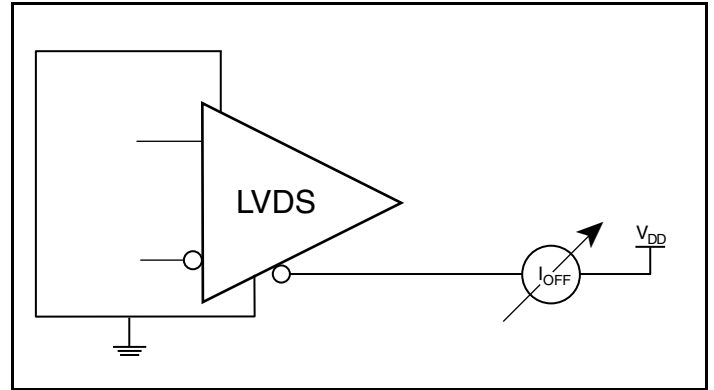


Propagation Delay

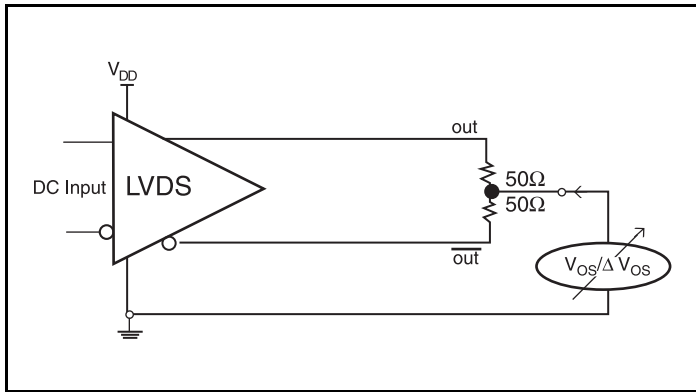
Parameter Measurement Information, continued



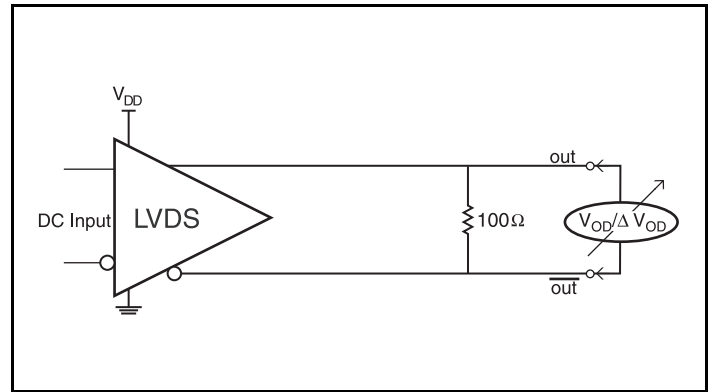
Output Rise/Fall Time



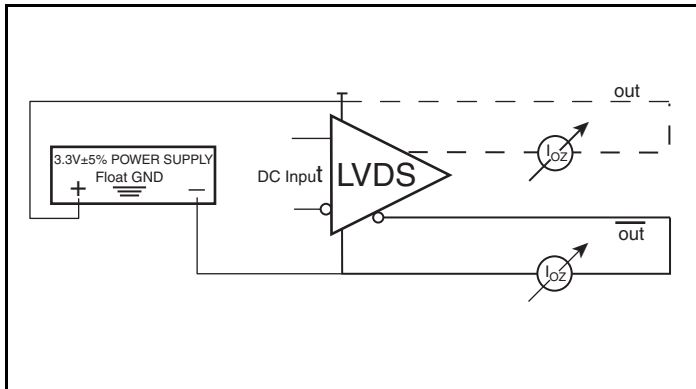
Power Off Leakage Setup



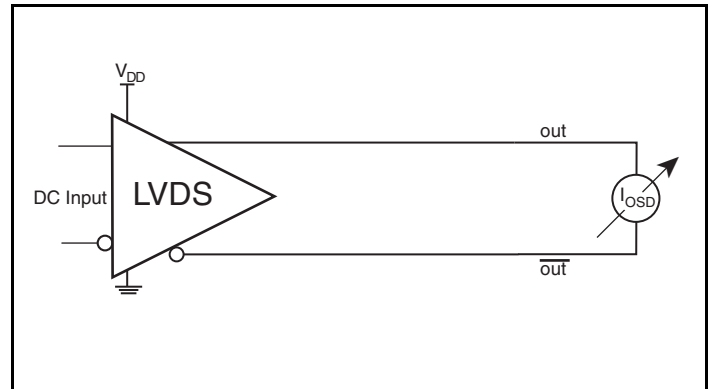
Offset Voltage Setup



Differential Output Voltage Setup

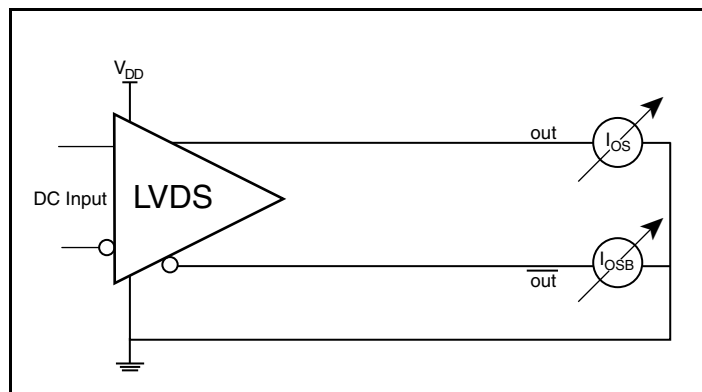


High Impedance Leakage Current Setup



Differential Output Short Circuit Setup

Parameter Measurement Information, continued



Output Short Circuit Current Setup

Applications Information

Recommendations for Unused Input and Output Pins

Inputs:

CLK Inputs

For applications not requiring the use of a clock input, it can be left floating. Though not required, but for additional protection, a 1k Ω resistor can be tied from the CLK input to ground.

LVC MOS Control Pins

All control pins have internal pull-ups or pull-downs; additional resistance is not required but can be added for additional protection. A 1k Ω resistor can be used.

Outputs:

LVDS Outputs

All unused LVDS output pairs can be either left floating or terminated with 100 Ω across. If they are left floating, there should be no trace attached.

LVDS Driver Termination

For a general LVDS interface, the recommended value for the termination impedance (Z_T) is between 90 Ω and 132 Ω . The actual value should be selected to match the differential impedance (Z_0) of your transmission line. A typical point-to-point LVDS design uses a 100 Ω parallel resistor at the receiver and a 100 Ω differential transmission-line environment. In order to avoid any transmission-line reflection issues, the components should be surface mounted and must be placed as close to the receiver as possible. IDT offers a full line of LVDS compliant devices with two types of output structures: current source and voltage source. The

standard termination schematic as shown in Figure 2 can be used with either type of output structure. Figure 3, which can also be used with both output types, is an optional termination with center tap capacitance to help filter common mode noise. The capacitor value should be approximately 50pF. If using a non-standard termination, it is recommended to contact IDT and confirm if the output structure is current source or voltage source type. In addition, since these outputs are LVDS compatible, the input receiver's amplitude and common-mode input range should be verified for compatibility with the output.

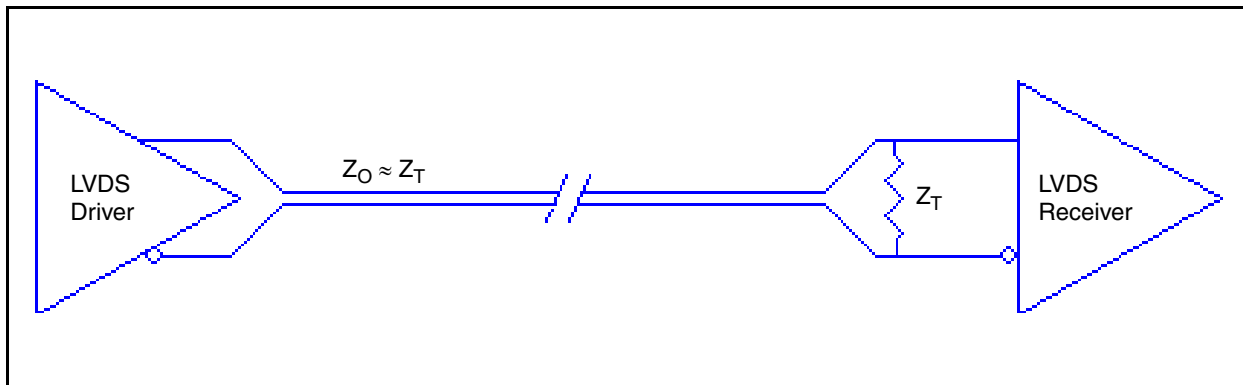


Figure 2. Standard LVDS Termination

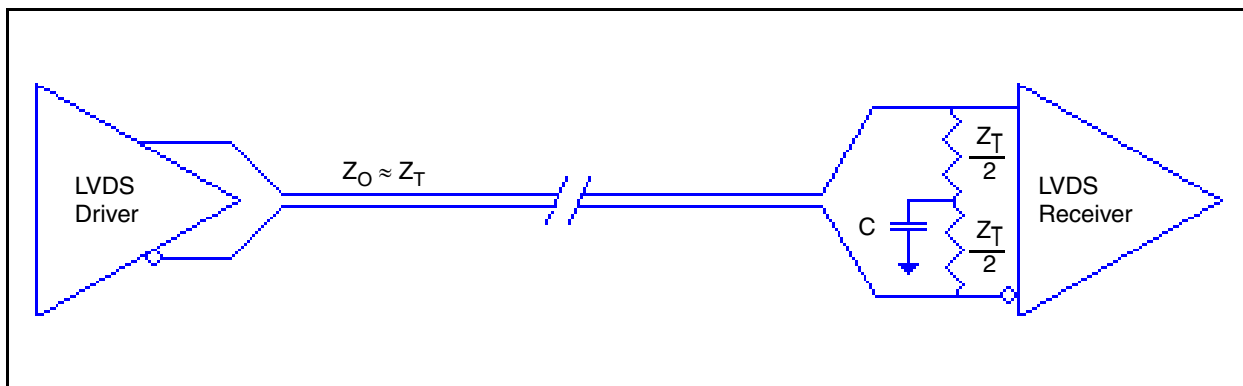


Figure 3. Optional LVDS Termination

Power Considerations

This section provides information on power dissipation and junction temperature for the 8545. Equations and example calculations are also provided.

1. Power Dissipation.

The total power dissipation for the 8545 is the sum of the core power plus the power dissipated in the load(s). The following is the power dissipation for $V_{DD} = 3.3V + 5\% = 3.465V$, which gives worst case results.

NOTE: Please refer to Section 3 for details on calculating power dissipated in the load.

- Power (core)_{MAX} = $V_{DD_MAX} * I_{DD_MAX} = 3.465V * 52mA = \mathbf{180.18mW}$

2. Junction Temperature.

Junction temperature, T_j , is the temperature at the junction of the bond wire and bond pad directly affects the reliability of the device. The maximum recommended junction temperature is 125°C. Limiting the internal transistor junction temperature, T_j , to 125°C ensures that the bond wire and bond pad temperature remains below 125°C.

The equation for T_j is as follows: $T_j = \theta_{JA} * Pd_{total} + T_A$

T_j = Junction Temperature

θ_{JA} = Junction-to-Ambient Thermal Resistance

Pd_{total} = Total Device Power Dissipation (example calculation is in section 1 above)

T_A = Ambient Temperature

In order to calculate junction temperature, the appropriate junction-to-ambient thermal resistance θ_{JA} must be used. Assuming a moderate air flow of 200 linear feet per minute and a multi-layer board, the appropriate value is 66.6°C/W per Table 6 below.

Therefore, T_j for an ambient temperature of 85°C with all outputs switching is:

$85^\circ C + 0.180W * 66.6^\circ C/W = 97^\circ C$. This is well below the limit of 125°C.

This calculation is only an example. T_j will obviously vary depending on the number of loaded outputs, supply voltage, air flow and the type of board (single layer or multi-layer).

Table 6. Thermal Resistance θ_{JA} for 20 Lead TSSOP, Forced Convection

Linear Feet per Minute	θ_{JA} by Velocity		
	0	200	500
Single-Layer PCB, JEDEC Standard Test Boards	114.5°C/W	98.0°C/W	88.0°C/W
Multi-Layer PCB, JEDEC Standard Test Boards	73.2°C/W	66.6°C/W	63.5°C/W

Reliability Information

Table 7. θ_{JA} vs. Air Flow Table for a 20 Lead TSSOP

θ_{JA} by Velocity			
Linear Feet per Minute	0	200	500
Single-Layer PCB, JEDEC Standard Test Boards	114.5°C/W	98.0°C/W	88.0°C/W
Multi-Layer PCB, JEDEC Standard Test Boards	73.2°C/W	66.6°C/W	63.5°C/W

Transistor Count

The transistor count for 8545 is: 644

Package Outline and Package Dimensions

Package Outline - G Suffix for 20 Lead TSSOP

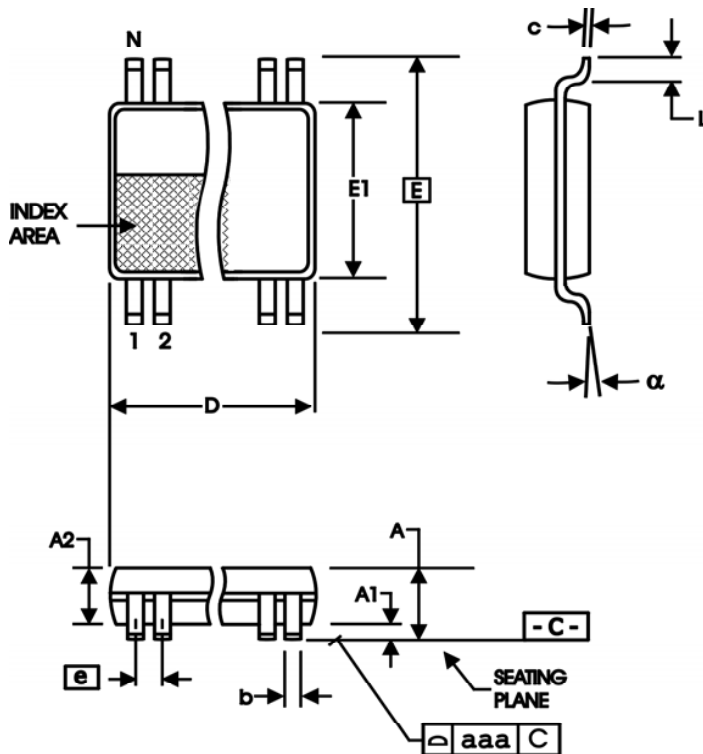


Table 8. Package Dimensions

All Dimensions in Millimeters		
Symbol	Minimum	Maximum
N	20	
A		1.20
A1	0.05	0.15
A2	0.80	1.05
b	0.19	0.30
c	0.09	0.20
D	6.40	6.60
E	6.40 Basic	
E1	4.30	4.50
e	0.65 Basic	
L	0.45	0.75
α	0°	8°
aaa		0.10

Reference Document: JEDEC Publication 95, MO-153

Ordering Information

Table 9. Ordering Information

Part/Order Number	Marking	Package	Shipping Packaging	Temperature
ICS8545BGILF	ICS8545BGILF	20 Lead TSSOP, Lead-Free	Tube	-40°C to 85°C
ICS8545BGILFT	ICS8545BGILF	20 Lead TSSOP, Lead-Free	Tape & Reel	-40°C to 85°C

Revision History Sheet

Rev	Table	Page	Description of Change	Date
B	T5	1	Features Section - added Additive Phase Jitter bullet.	5/31/07
		5	AC Characteristics Table - added Additive Phase Jitter spec.	
		6	Added <i>Additive Phase Jitter Plot</i> .	
		11	Added <i>Power Considerations</i> section.	
B	T9	13	Ordering Information Table - added lead-free marking.	2/15/08
B	T9	13	Removed leaded orderable parts from Ordering Information table	11/15/12
C		10	Updated LVDS Driver Termination application note.	12/8/15
			Deleted HiperClocks references throughout the datasheet.	
			Updated header/footer.	
			Deleted "ICS" prefix and "I" suffix from part number.	

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